

Sn. 09/844,481

Attorney Docket No. FUJI:185

B<sup>1</sup> wherein the alternating conductivity type layer comprises first semiconductor regions of a first conductivity type and second semiconductor regions of a second conductivity type;

wherein the first semiconductor regions and the second semiconductor regions are alternately arranged in a surface portion of the major surface;

wherein the alternating conductivity type layer comprises a closed loop formed by the first and second semiconductor regions alternately arranged along the direction of the closed loop and surrounding one of the main electrodes; and

wherein the alternating conductivity type layer comprises at least one straight section and at least one curved section.--

B2 pulca27 --4. (Amended) The lateral semiconductor device according to Claim 1, wherein the alternating conductivity type layer comprises at least two straight sections and at least two curved sections.--

B3 pulca27 --5. (Twice Amended) A lateral semiconductor device comprising:  
a semiconductor chip;  
two main electrodes on one major surface of the semiconductor chip; and  
an alternating conductivity type layer between the main electrodes;  
wherein the alternating conductivity type layer comprises first semiconductor regions of a first conductivity type and second semiconductor regions of a second conductivity type;  
wherein the first semiconductor regions and the second semiconductor regions are alternately arranged;  
wherein the alternating conductivity type layer comprises a closed loop surrounding one of the main electrodes;  
wherein the alternating conductivity type layer comprises at least one straight section and at least one curved section; and  
wherein the first semiconductor regions and the second semiconductor regions are arranged alternately at a first pitch in the straight section, and the first semiconductor regions and the second semiconductor regions are arranged alternately at a second pitch in

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B3 the curved section.--

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B4 subc2> --8. (Amended) The lateral semiconductor device according to Claim 6, wherein the curved section is doped substantially more lightly than the straight section.

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9. (Amended) The lateral semiconductor device according to Claim 8, wherein the curved section is substantially intrinsic.--

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B5 subc2> --11. (Amended) The lateral semiconductor device according to Claim 8, wherein the curved section is doped with an n-type impurity and a p-type impurity.

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12. (Amended) The lateral semiconductor device according to Claim 9, wherein the curved section is doped with an n-type impurity and a p-type impurity.--

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B6 subc2> --14. (Amended) The lateral semiconductor device according to Claim 1, further comprising a plurality of closed loops, each including the alternating conductivity type layer.--

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